

2SK2315

Silicon N Channel MOS FET

REJ03G1006-0200
(Previous: ADE-208-1354)
Rev.2.00
Sep.07,2005

Application

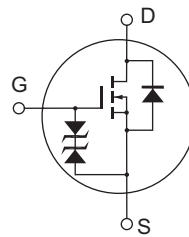
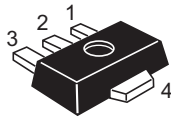
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 2.5 V gate drive device can be driven from 3 V source.
- Suitable for DC-DC converter, motor drive, power switch, solenoid drive

Outline

RENESAS Package code: PLZZ0004CA-A
(Package name: UPAK[®])



1. Gate
2. Drain
3. Source
4. Drain

Note: Marking is "TY"

*UPAK is a trademark of Renesas Technology Corp.

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	2	A
Drain peak current	$I_{D(pulse)}^{*1}$	4	A
Body to drain diode reverse drain current	I_{DR}	2	A
Channel dissipation	P_{ch}^{*2}	1	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

- Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1 \%$
 2. When using the alumina ceramic board ($12.5 \times 20 \times 0.7 \text{mm}$)

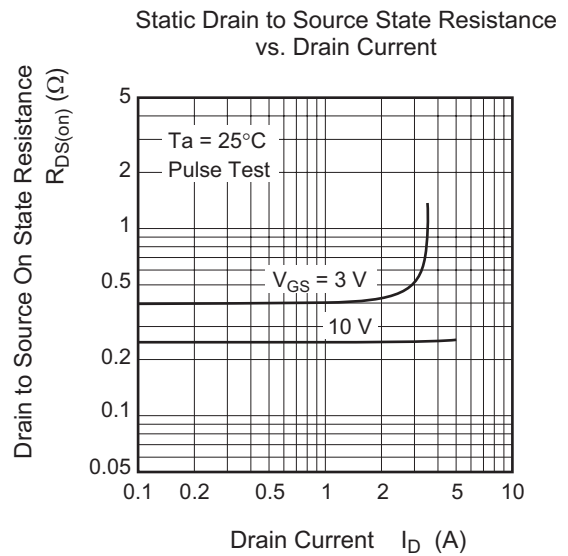
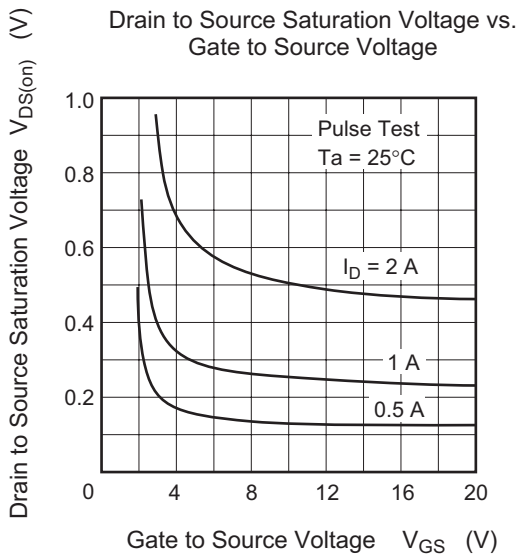
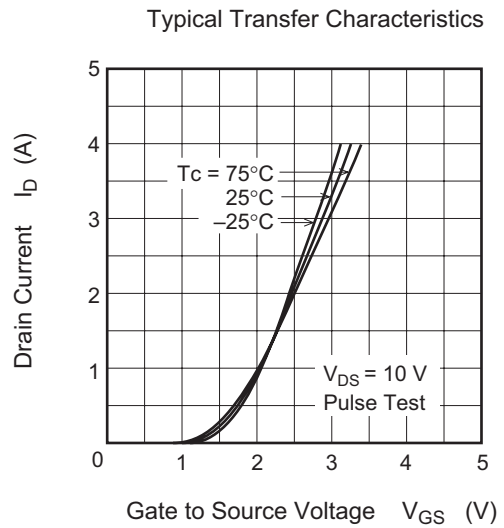
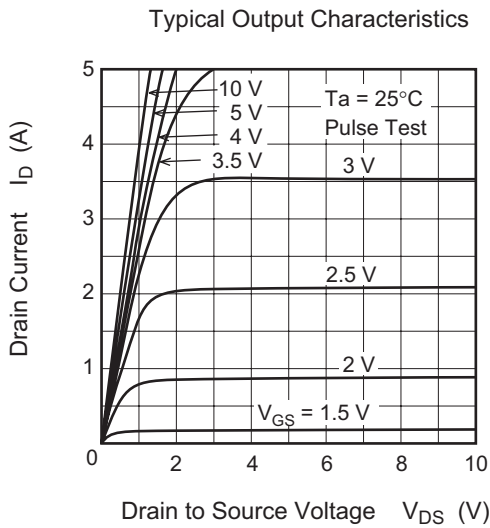
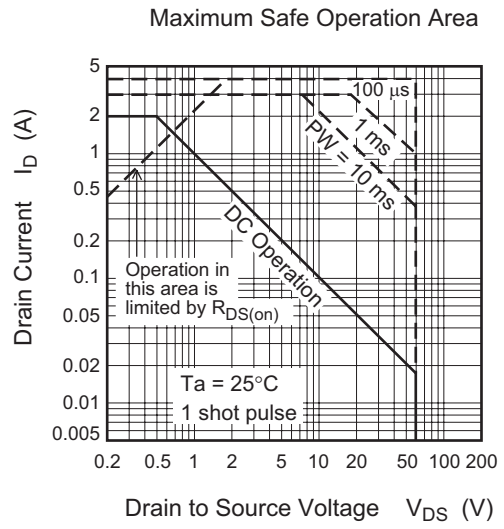
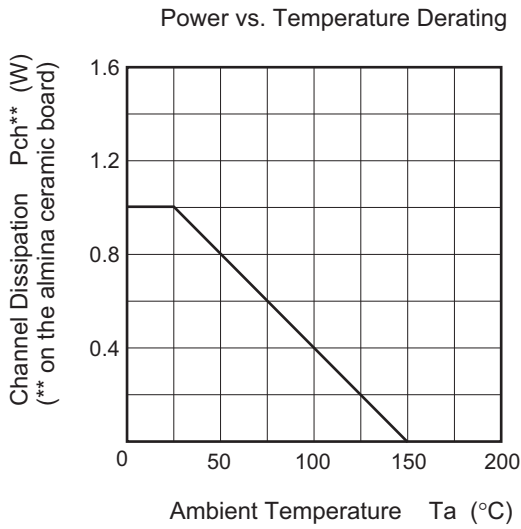
Electrical Characteristics

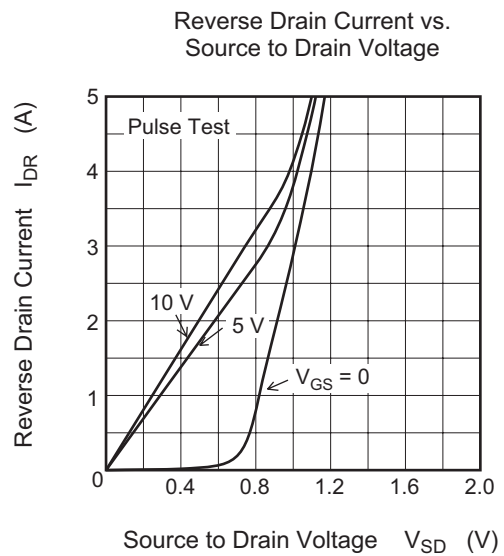
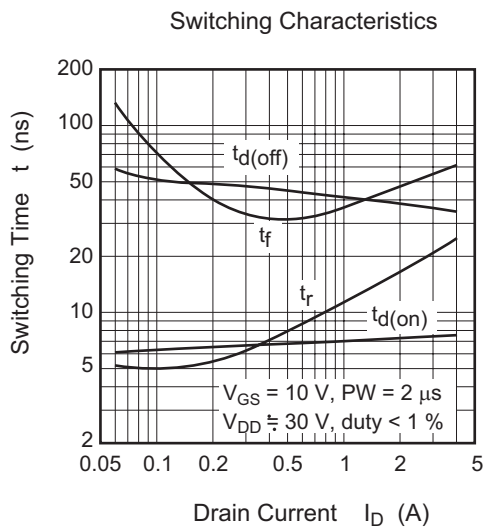
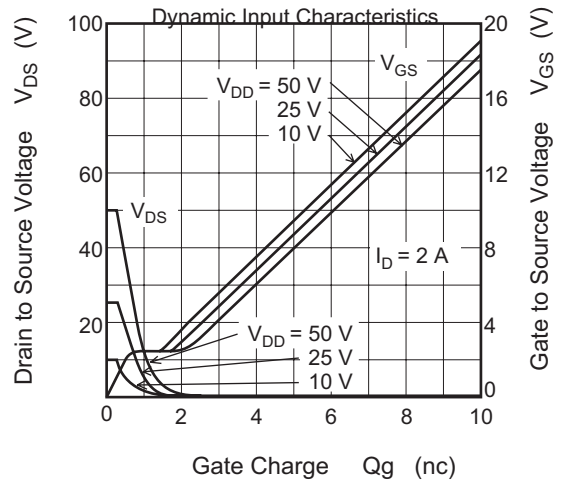
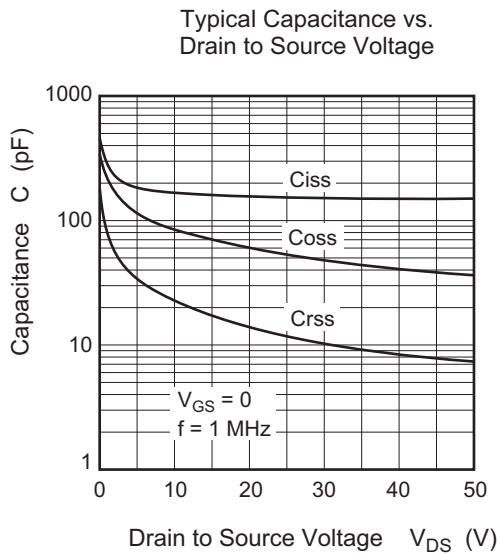
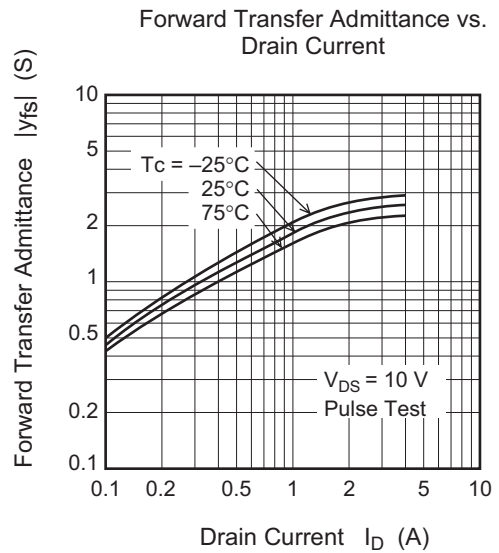
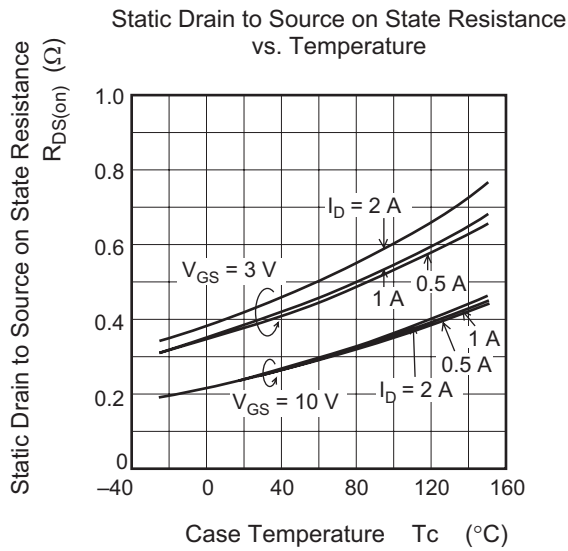
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 5	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	5	μA	$V_{DS} = 50 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.5	—	1.5	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.4	0.6	Ω	$I_D = 0.3 \text{ A}$, $V_{GS} = 3 \text{ V}^{*3}$
		—	0.35	0.45	Ω	$I_D = 1 \text{ A}$, $V_{GS} = 4 \text{ V}^{*3}$
Forward transfer admittance	$ y_{fs} $	1.5	1.8	—	S	$I_D = 1 \text{ A}$, $V_{DS} = 10 \text{ V}^{*3}$
Input capacitance	C_{iss}	—	173	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	85	—	pF	
Reverse transfer capacitance	C_{rss}	—	23	—	pF	
Turn-on time	t_{on}	—	21	—	ns	$I_D = 1 \text{ A}$, $R_L = 30 \Omega$,
Turn-off time	t_{off}	—	85	—	ns	$V_{GS} = 10 \text{ V}$

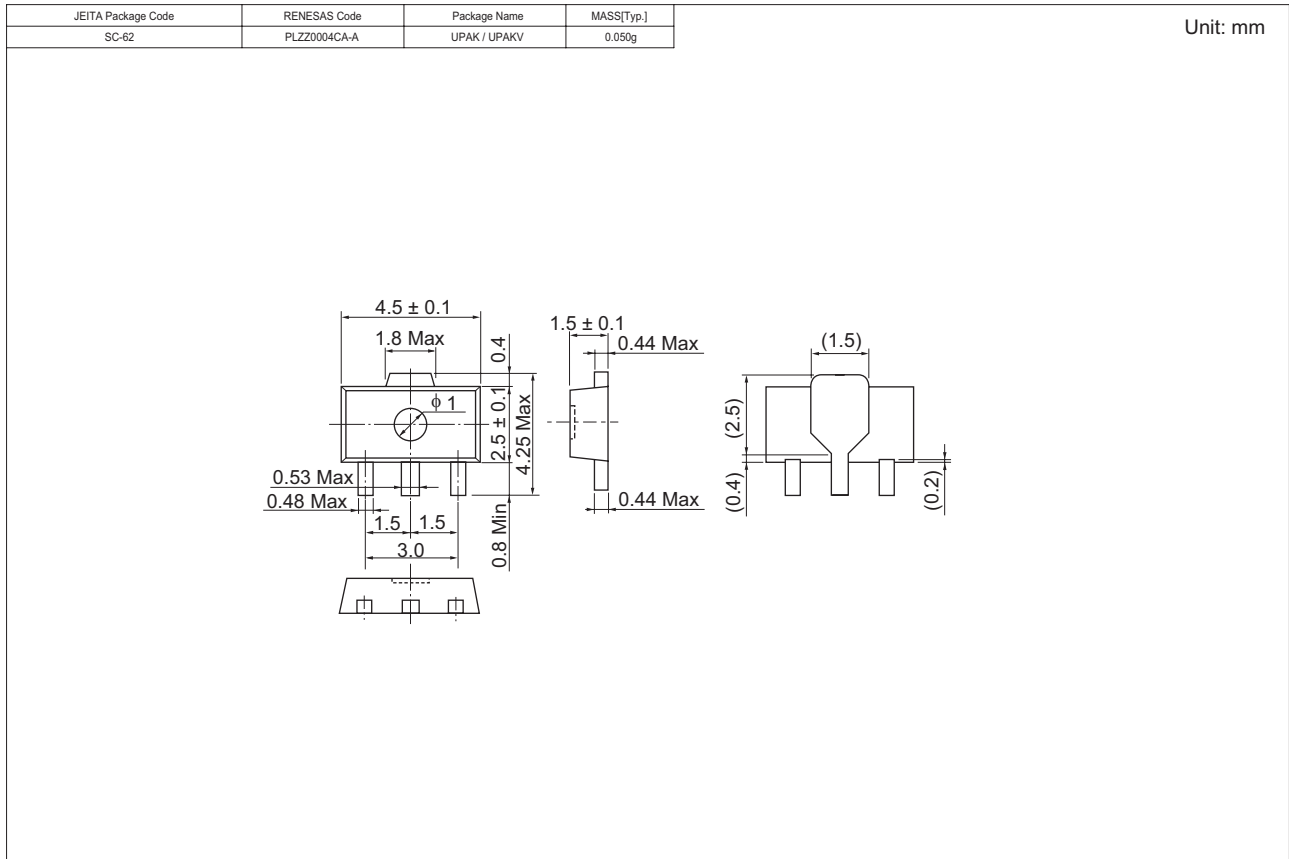
Note: 3. Pulse Test

Main Characteristics





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK2315TYTL-E	1000 pcs	Taping
2SK2315TYTR-E	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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